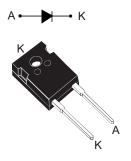




# 650 V, 30 A high surge silicon carbide power Schottky diode



DO-247 LL



#### Product label



#### **Product status link**

STPSC30G065

Product summary				
I <sub>F(AV)</sub>	30 A			
V <sub>RRM</sub>	650 V			
T <sub>j</sub> (max.)	175 °C			
V <sub>F</sub> (typ.)	1.30 V			

#### **Features**

- No reverse recovery charge in application current range
- · Switching behavior independent of temperature
- · High forward surge capability
- Operating T<sub>i</sub> from -55 °C to 175 °C
- ECOPACK2 compliant component

## **Applications**

- Solar inverter
- Air conditioning equipment
- UPS power supply
- Telecom / Server power equipment
- OBC (On board battery chargers)
- EV Charging station

#### **Description**

The SiC diode STPSC30G065, moulded in DO-247 LL with long leads, is an ultrahigh performance power Schottky rectifier. It is manufactured using a silicon carbide substrate. The wide band-gap material allows the design of a low  $V_{\rm F}$  Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Based on latest technology optimization, this diode has an improved forward surge current capability, making it ideal for use in PFC, where this ST SiC diode boosts the performance in hard switching conditions. Using the latest design improvement of the "G" series of ST SiC diodes, as well as implemented tests in production, this diode is becoming the reference point in the combination of efficiency and application robustness to the application design.



## 1 Characteristics

Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)

Symbol		Value	Unit		
V <sub>RRM</sub>	Repetitive peak reverse voltage (T <sub>j</sub> = -55 °C to +175 °C)			650	V
I <sub>F(RMS)</sub>	Forward rms current				Α
I <sub>F(AV)</sub>	Average forward current	T <sub>c</sub> = 130 °C, δ = 1	T <sub>c</sub> = 130 °C, δ = 1		
I <sub>FRM</sub>	Repetitive peak forward current	$T_c = 130 ^{\circ}\text{C},  T_j = 175 ^{\circ}\text{C},  \delta = 0.1,  f_{\text{SW}} > 10 \text{kHz}$		124	Α
	I <sub>FSM</sub> Surge non repetitive forward current	$t_{\rm p}$ = 10 ms sinusoidal	T <sub>c</sub> = 25 °C	195	
I <sub>FSM</sub>		t <sub>p</sub> = 10 ms sinusoidai	T <sub>c</sub> = 150 °C	156	Α
		t <sub>p</sub> = 10 μs square	T <sub>c</sub> = 25 °C	1100	
T <sub>stg</sub>	Storage temperature range	-65 to +175	°C		
Tj	Operating junction temperature range			-55 to +175	°C

Table 2. Thermal resistance parameters

Symbol	Parameter	Va	llue	Unit
Symbol	raiametei	Тур.	Max.	Offic
R <sub>th(j-c)</sub>	Junction to case	0.60	0.85	°C/W

For more information, please refer to the following application note:

AN5088: Rectifiers thermal management, handling and mounting recommendations

Table 3. Static electrical characteristics

Symbol	Parameter Test conditions		nditions	Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	T <sub>j</sub> = 25 °C	V <sub>R</sub> = V <sub>RRM</sub>	-	25	300	μА
IR ( )		T <sub>j</sub> = 175 °C		-	150	1200	
V <sub>E</sub> <sup>(2)</sup> Forward voltage drop		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 30 A	-	1.30	1.45	V
VF (2)	Forward voltage drop	T <sub>j</sub> = 175 °C	IF - 30 A	-	1.49	1.70	<b>v</b>

- 1. Pulse test:  $t_p$  = 10 ms,  $\delta$  < 2%
- 2. Pulse test:  $t_p$  = 380  $\mu$ s,  $\delta$  < 2%

To evaluate the conduction losses, use the following equation:

$$P = 0.879 \times I_{F(AV)} + 0.027 \times I_{F}^{2}_{(RMS)}$$

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses on a power diode

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**Table 4. Dynamic electrical characteristics** 

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Q <sub>Cj</sub> (1)	Total capacitive charge	V <sub>R</sub> = 400 V	-	86	-	nC
Ci	Total conscitones	V <sub>R</sub> = 0 V, T <sub>c</sub> = 25 °C, F = 1 MHz	-	1890	-	pF
C <sub>j</sub> Total capacitance	V <sub>R</sub> = 400 V, T <sub>C</sub> = 25 °C, F = 1 MHz	-	120	-	pΕ	

1. Most accurate value for the capacitive charge:  $Q_{cj}(V_R) = \int\limits_0^{V_{out}} C_j(V_R) dV_R$ 

Figure 1. Thermal transient impedance model circuit of the diode –  $Z_{th(j-c)}$ 

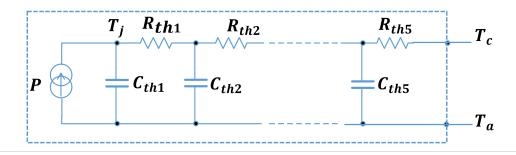


Table 5. Components typical values of the diode thermal transient impedance model Z<sub>th(j-c)</sub>

Ref.	Value (K/W)	Ref.	Value (J/K)
R <sub>th1</sub>	19.43 m	C <sub>th1</sub>	1.71 m
R <sub>th2</sub>	175.31 m	C <sub>th2</sub>	1.73 m
R <sub>th3</sub>	184.79 m	C <sub>th3</sub>	9.54 m
R <sub>th4</sub>	169.61 m	C <sub>th4</sub>	51.54 m
R <sub>th5</sub>	50.39 m	C <sub>th5</sub>	627.76 m

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10

0.0 0.2

0.6

0.8 1.0 1.2 1.4 1.6 1.8 2.0

0.4

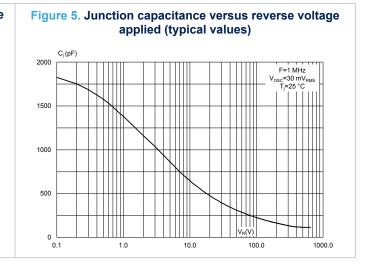
## 1.1 Characteristics (curves)

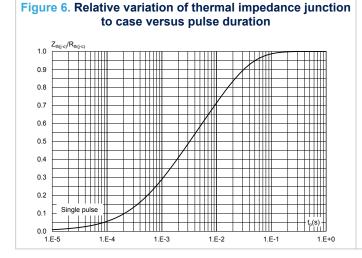
Figure 2. Forward voltage drop versus forward current (typical values)

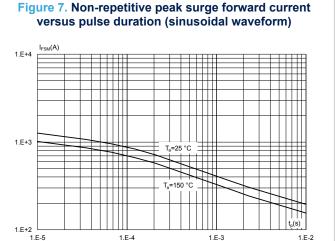
2.2

1.E+2
1.E+1
1.E+2
1.E+1
1.E+2
1.E+1
1.E+2
1.E+1
1.E+2
1.E+1
1.E+1
1.E+2

Figure 4. Peak forward current versus case temperature  $(f_{SW} > 10 \text{ kHz})$ 250 200 150  $\delta = 0.3$ 100 δ=0.5 δ=0.7 0 25 50 75 100 125 150 175

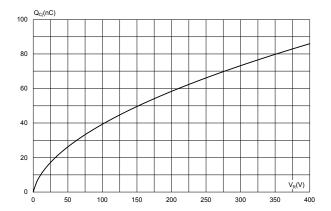






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Figure 8. Total capacitive charges versus reverse voltage applied (typical values)



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# Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

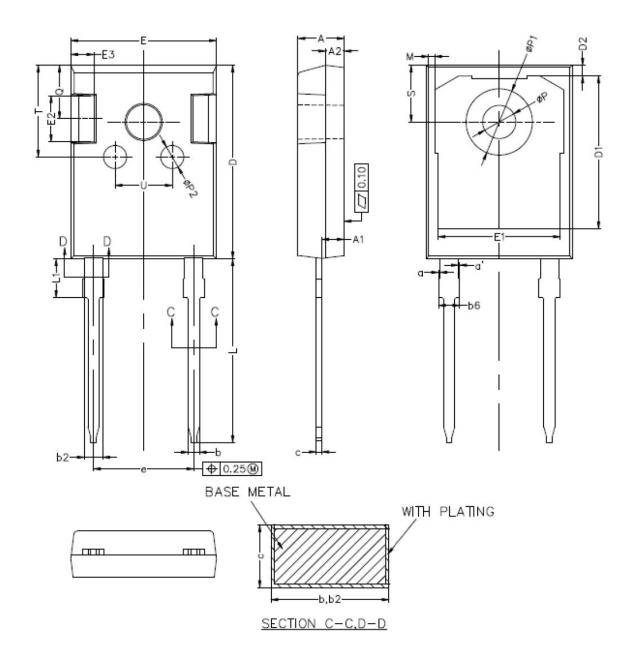
#### 2.1 DO-247 LL package information

• Epoxy meets UL94, V0

Cooling method: by conduction (C)
Recommended torque value: 0.8 N·m

Maximum torque value: 1.0 N·m

Figure 9. DO-247 LL package outline



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Note:

This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. DO-247 LL package mechanical data

			Dime	nsions		
Ref.		Millimeters Inches (fo		s (for reference	only)	
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	4.90	5.00	5.10	0.192	0.197	0.201
A1	2.31	2.41	2.51	0.090	0.095	0.099
A2	1.90	2.00	2.10	0.074	0.079	0.083
а	0.00		0.15	0.000		0.006
a'	0.00		0.15	0.000		0.006
b	1.16		1.29	0.045		0.051
b2	1.96		2.06	0.077		0.082
b6			2.25			0.089
С	0.59		0.66	0.023		0.026
D	20.90	21.00	21.10	0.822	0.827	0.831
D1	16.25	16.55	16.85	0.639	0.652	0.664
D2	1.05	1.20	1.35	0.041	0.047	0.054
E	15.70	15.80	15.90	0.618	0.622	0.626
E1	13.06	13.26	13.46	0.514	0.522	0.530
E2	4.90	5.00	5.10	0.192	0.197	0.201
E3	2.40	2.50	2.60	0.094	0.098	0.103
е	10.78	10.88	10.98	0.424	0.428	0.433
L	19.80	19.92	20.10	0.779	0.784	0.792
L1	3.93		4.46	0.154		0.176
М	0.35		0.95	0.013		0.038
Р	3.50	3.60	3.70	0.137	0.142	0.146
P1	7.00		7.40	0.275		0.292
P2	2.40	2.50	2.60	0.094	0.098	0.103
Q	5.60		6.00	0.220		0.237
S	6.05	6.15	6.25	0.238	0.242	0.247
Т	9.80		10.20	0.385		0.402
U	6.00		6.40	0.236		0.252

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# 3 Ordering information

**Table 7. Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC30G065WL	STPSC30G065WL	DO-247 LL	5.9 g	30	Tube

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# **Revision history**

Table 8. Document revision history

Date	Revision	Changes
06-Dec-2024	1	Initial release.

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